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IN THE CLAIMS

1. (currently amended): A semiconductor light emitting device, comprising:
a semiconductor layered portion having a light emitting layer forming portion;
a conductive substrate; and
a metal layer for adhering said semiconductor layered portion to said conductive substrate,

wherein said metal layer includes at least a first metal layer for making ohmic contact with said semiconductor layered portion, a second metal layer essentially consisted of Ag, and a third metal layer made of a metal which allows to adhere to said conductive substrate and said semiconductor layered portion at a low temperature;

wherein said third metal layer comprises at least one selected from a group of In, In-Zn alloy, and Sn-Zn alloy.

2. (original): The semiconductor light emitting device according to claim 1, wherein said first metal layer is partially removed so as to form a missing portion.

3. (original): The semiconductor light emitting device according to claim 2, wherein said missing portion occupies 50% or less of a surface area of said semiconductor layered portion.

4. (original): The semiconductor light emitting device according to claim 2, wherein a protective film is provided in said missing portion, said protection film being a film for preventing the Ag in said second metal layer from diffusing into said semiconductor layered portion, and for transmitting light emitted in said light emitting layer forming portion.

5. (original): The semiconductor light emitting device according to claim 4, wherein said protective film is made of SiO₂ or Al₂O₃.

6. (original): The semiconductor light emitting device according to claim 1, wherein Ag is added to said first metal layer.

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7. (original): The semiconductor light emitting device according to claim 1, wherein said second metal layer contains at least either Zn or Au at 10 atomic % or less, and comprises Ag at 90 atomic % or greater.

8. (original): The semiconductor light emitting device according to claim 1, wherein said second metal layer is formed to have a thickness of from 0.1 to 0.5 mm.

9. (canceled)

10. (original): The semiconductor light emitting device according to claim 1, wherein said conductive substrate is formed of a semiconductor substrate, and a fourth metal layer for making an ohmic contact with said semiconductor substrate is provided on a side of said metal layer, said side being contact with said semiconductor substrate.

11. (original): The semiconductor light emitting device according to claim 10, wherein said fourth metal layer is made of at least one selected from a group of an Au-Zn alloy, an Au-Be alloy, and an Au-Ge alloy.

12. (new): A semiconductor light emitting device, comprising:
a semiconductor layered portion having a light emitting layer forming portion;
a conductive substrate; and
a metal layer for adhering said semiconductor layered portion to said conductive substrate,

wherein said metal layer includes at least a first metal layer for making ohmic contact with said semiconductor layered portion, a second metal layer essentially consisted of Ag, and a third metal layer made of a metal which allows to adhere to said conductive substrate and said semiconductor layered portion at a low temperature;

wherein said first metal layer is partially removed so as to form a missing portion.

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13. (new): The semiconductor light emitting device according to claim 12, wherein said missing portion occupies 50% or less of a surface area of said semiconductor layered portion.

14. (new): The semiconductor light emitting device according to claim 12, wherein a protective film is provided in said missing portion, said protection film being a film for preventing the Ag in said second metal layer from diffusing into said semiconductor layered portion, and for transmitting light emitted in said light emitting layer forming portion.

15. (new): The semiconductor light emitting device according to claim 14, wherein said protective film is made of SiO_2 or Al_2O_3 .

16. (new): The semiconductor light emitting device according to claim 12, wherein Ag is added to said first metal layer.

17. (new): The semiconductor light emitting device according to claim 12, wherein said conductive substrate is formed of a semiconductor substrate, and a fourth metal layer for making an ohmic contact with said semiconductor substrate is provided on a side of said metal layer, said side being contact with said semiconductor substrate.

18. (new): A semiconductor light emitting device, comprising:
a semiconductor layered portion having a light emitting layer forming portion;
a conductive substrate; and
a metal layer for adhering said semiconductor layered portion to said conductive substrate,

wherein said metal layer includes at least a first metal layer for making ohmic contact with said semiconductor layered portion, a second metal layer essentially consisted of Ag, and a third metal layer made of a metal which allows to adhere to said conductive substrate and said semiconductor layered portion at a low temperature; and

wherein Ag is added to said first metal layer.

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19. (new): The semiconductor light emitting device according to claim 18, wherein said conductive substrate is formed of a semiconductor substrate, and a fourth metal layer for making an ohmic contact with said semiconductor substrate is provided on a side of said metal layer, said side being contact with said semiconductor substrate.

20. (new): The semiconductor light emitting device according to claim 19, wherein said fourth metal layer is made of at least one selected from a group of an Au-Zn alloy, an Au-Be alloy, and an Au-Ge alloy.

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